# **Analog Multiplexer/ Demultiplexer**

# **High-Performance Silicon-Gate CMOS**

The MC74LVXT8051 utilizes silicon–gate CMOS technology to achieve fast propagation delays, low ON resistances, and low OFF leakage currents. This analog multiplexer/demultiplexer controls analog voltages that may vary across the complete power supply range (from  $V_{CC}$  to GND).

The LVXT8051 is similar in pinout to the high–speed HC4051A and the metal–gate MC14051B. The Channel–Select inputs determine which one of the Analog Inputs/Outputs is to be connected by means of an analog switch to the Common Output/Input. When the Enable pin is HIGH, all analog switches are turned off.

The Channel–Select and Enable inputs are compatible with TTL–type input thresholds. The input protection circuitry on this device allows overvoltage tolerance on the input, allowing the device to be used as a logic–level translator from 3.0 V CMOS logic to 5.0V CMOS Logic or from 1.8V CMOS logic to 3.0 V CMOS Logic while operating at the higher–voltage power supply.

The MC74LVXT8051 input structure provides protection when voltages up to 7.0 V are applied, regardless of the supply voltage. This allows the MC74LVXT8051 to be used to interface 5.0 V circuits to 3.0 V circuits.

This device has been designed so that the ON resistance  $(R_{on})$  is more linear over input voltage than  $R_{on}$  of metal-gate CMOS analog switches.

# **Features**

- Fast Switching and Propagation Speeds
- Low Crosstalk Between Switches
- Diode Protection on All Inputs/Outputs
- Analog Power Supply Range  $(V_{CC} GND) = 2.0$  to 6.0 V
- Digital (Control) Power Supply Range  $(V_{CC} GND) = 2.0$  to 6.0 V
- Improved Linearity and Lower ON Resistance Than Metal–Gate Counterparts
- Low Noise
- In Compliance With the Requirements of JEDEC Standard No. 7A
- These Devices are Pb-Free and are RoHS Compliant



# ON Semiconductor®

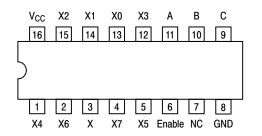
http://onsemi.com



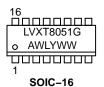


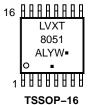


## **PIN ASSIGNMENT**



# MARKING DIAGRAMS





LVXT8051 = Specific Device Code A = Assembly Location

WL, L = Wafer Lot Y = Year WW, W = Work Week G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

# **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 10 of this data sheet.

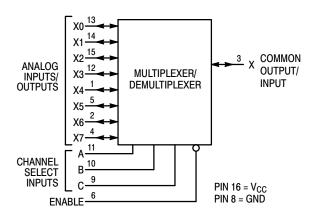


Figure 1. LOGIC DIAGRAM Single-Pole, 8-Position Plus Common Off

# **FUNCTION TABLE - MC74LVXT8051**

Conti	rol Inp			
	,	Select	t	
Enable	С	В	Α	ON Channels
L	L	L	L	X0
L	L	L	Н	X1
L	L	Н	L	X2
L	L	Н	Н	X3
L	Н	L	L	X4
L	Н	L	Н	X5
L	Н	Н	L	X6
L	Н	Н	Н	X7
Н	Х	Χ	Χ	NONE

X = Don't Care

# **MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Positive DC Supply Voltage (Referenced to GND)	-0.5 to + 7.0	V
V <sub>IS</sub>	Analog Input Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
V <sub>in</sub>	Digital Input Voltage (Referenced to GND)	-0.5 to V <sub>CC</sub> + 0.5	V
I	DC Current, Into or Out of Any Pin	-20	mA
P <sub>D</sub>	Power Dissipation in Still Air, SOIC Package† TSSOP Package†	500 450	mW
T <sub>stg</sub>	Storage Temperature Range	-65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

†Derating: SOIC Package: -7 mW/°C from 65° to 125°C TSSOP Package: -6.1 mW/°C from 65° to 125°C This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$   $V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V<sub>CC</sub>). Unused outputs must be left open.

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	Positive DC Supply Voltage (Referenced to GND)	2.0	6.0	V
V <sub>IS</sub>	Analog Input Voltage	0.0	V <sub>CC</sub>	V
V <sub>in</sub>	Digital Input Voltage (Referenced to GND)	GND	V <sub>CC</sub>	V
V <sub>IO</sub> *	Static or Dynamic Voltage Across Switch		1.2	V
T <sub>A</sub>	Operating Temperature Range, All Package Types	-55	+85	°C
t <sub>r</sub> , t <sub>f</sub>		3.3 V ± 0.3 V 0 5.0 V ± 0.5 V 0	100 20	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond

# **DC CHARACTERISTICS – Digital Section** (Voltages Referenced to GND)

			V <sub>CC</sub> Guara	nteed Lim			
Symbol	Parameter	Condition	v	−55 to 25°C	≤85°C	≤125°C	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage, Channel-Select or Enable Inputs	R <sub>on</sub> = Per Spec	3.0 4.5 5.5	1.2 2.0 2.0	1.2 2.0 2.0	1.2 2.0 2.0	V
V <sub>IL</sub>	Maximum Low–Level Input Voltage, Channel–Select or Enable Inputs	R <sub>on</sub> = Per Spec	3.0 4.5 5.5	0.53 0.8 0.8	0.53 0.8 0.8	0.53 0.8 0.8	V
I <sub>in</sub>	Maximum Input Leakage Current, Channel–Select or Enable Inputs	V <sub>in</sub> = V <sub>CC</sub> or GND	5.5	±0.1	±1.0	±1.0	μΑ
I <sub>CC</sub>	Maximum Quiescent Supply Current (per Package)	Channel Select, Enable and V <sub>IS</sub> = V <sub>CC</sub> or GND; V <sub>IO</sub> = 0 V	5.5	4	40	160	μΑ

# DC ELECTRICAL CHARACTERISTICS Analog Section

			V <sub>CC</sub>	Guar	anteed Lim	nit	
Symbol	Parameter	Test Conditions	V	-55 to 25°C	≤ <b>85</b> ° <b>C</b>	≤125°C	Unit
R <sub>on</sub>	Maximum "ON" Resistance	$V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{IS} = V_{CC} \text{ to GND}$ $ I_S  \le 10.0 \text{ mA (Figures 1, 2)}$	3.0 4.5 5.5	40 30 25	45 32 28	50 37 30	Ω
		$V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{IS} = V_{CC} \text{ or GND (Endpoints)}$ $ I_S  \le 10.0 \text{ mA (Figures 1, 2)}$	3.0 4.5 5.5	30 25 20	35 28 25	40 35 30	
$\Delta R_{on}$	Maximum Difference in "ON" Resistance Between Any Two Channels in the Same Package	$V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{IS} = 1/2 (V_{CC} - GND)$ $ I_S  \le 10.0 \text{ mA}$	3.0 4.5 5.5	15 8.0 8.0	20 12 12	25 15 15	Ω
I <sub>off</sub>	Maximum Off–Channel Leakage Current, Any One Channel	$V_{in} = V_{IL}$ or $V_{IH}$ ; $V_{IO} = V_{CC}$ or GND; Switch Off (Figure 3)	5.5	0.1	0.5	1.0	μΑ
	Maximum Off–Channel Leakage Current, Common Channel	$V_{in} = V_{IL} \text{ or } V_{IH};$ $V_{IO} = V_{CC} \text{ or GND};$ Switch Off (Figure 4)	5.5	0.2	2.0	4.0	
I <sub>on</sub>	Maximum On–Channel Leakage Current, Channel–to–Channel	$V_{in} = V_{IL}$ or $V_{IH}$ ; Switch-to-Switch = $V_{CC}$ or GND; (Figure 5)	5.5	0.2	2.0	4.0	μΑ

the Recommended Operating Ranges limits may affect device reliability.

\*For voltage drops across switch greater than 1.2 V (switch on), excessive V<sub>CC</sub> current may be drawn; i.e., the current out of the switch may contain both V<sub>CC</sub> and switch input components. The reliability of the device will be unaffected unless the Maximum Ratings are exceeded.

# AC CHARACTERISTICS ( $C_L = 50 \text{ pF}$ , Input $t_r = t_f = 3 \text{ ns}$ )

			v <sub>cc</sub>	Guara	1		
Symbol	Parameter		v	-55 to 25°C	≤ <b>85</b> °C	≤125°C	Unit
t <sub>PLH</sub> ,	Maximum Propagation Delay, Channel-Sele	ect to Analog Output	2.0	30	35	40	ns
$t_{PHL}$	(Figure 9)		3.0	20	25	30	
			4.5	15	18	22	
			5.5	15	18	20	
t <sub>PLH</sub> ,	Maximum Propagation Delay, Analog Input t	to Analog Output	2.0	4.0	6.0	8.0	ns
$t_{PHL}$	(Figure 10)		3.0	3.0	5.0	6.0	
			4.5	1.0	2.0	2.0	
			5.5	1.0	2.0	2.0	
$t_{PLZ}$ ,	Maximum Propagation Delay, Enable to Ana	alog Output	2.0	30	35	40	ns
t <sub>PHZ</sub>	(Figure 11)		3.0	20	25	30	
			4.5	15	18	22	
			5.5	15	18	20	
$t_{PZL}$ ,	Maximum Propagation Delay, Enable to Ana	alog Output	2.0	20	25	30	ns
$t_{PZH}$	(Figure 11)		3.0	12	14	15	
			4.5	8.0	10	12	
			5.5	8.0	10	12	
C <sub>in</sub>	Maximum Input Capacitance, Channel-Sele	ect or Enable Inputs		10	10	10	pF
C <sub>I/O</sub>	Maximum Capacitance	Analog I/O		35	35	35	pF
	(All Switches Off)	Common O/I		130	130	130	
		Feedthrough		1.0	1.0	1.0	

		Typical @ 25°C, V <sub>CC</sub> = 5.0 V	
$C_{PD}$	Power Dissipation Capacitance (Figure 13)*	45	рF

<sup>\*</sup> Used to determine the no–load dynamic power consumption:  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ .

# **ADDITIONAL APPLICATION CHARACTERISTICS** (GND = 0 V)

			V <sub>CC</sub>	Limit*	
Symbol	Parameter	Condition	v	25°C	Unit
BW	Maximum On–Channel Bandwidth or Minimum Frequency Response (Figure 6)	$\begin{array}{l} f_{in} = \text{1MHz Sine Wave; Adjust } f_{in} \text{ Voltage to Obtain} \\ \text{0dBm at V}_{OS}; \text{ Increase } f_{in} \text{ Frequency Until dB Meter} \\ \text{Reads } -3\text{dB;} \\ \text{R}_L = 50\Omega, C_L = 10\text{pF} \end{array}$	3.0 4.5 5.5	80 80 80	MHz
_	Off-Channel Feedthrough Isolation (Figure 7)	$f_{in}$ = Sine Wave; Adjust $f_{in}$ Voltage to Obtain 0dBm at $V_{IS}$ $f_{in}$ = 10kHz, $R_L$ = 600 $\Omega$ , $C_L$ = 50pF	3.0 4.5 5.5	-50 -50 -50	dB
		$f_{in} = 1.0MHz, R_L = 50\Omega, C_L = 10pF$	3.0 4.5 5.5	-37 -37 -37	
_	Feedthrough Noise. Channel–Select Input to Common I/O (Figure 8)	$V_{in} \le 1 \text{MHz Square Wave } (t_r = t_f = 3 \text{ns}); \text{ Adjust } R_L \text{ at Setup so that } I_S = 0 \text{A}; \\ \text{Enable} = \text{GND} \qquad \qquad R_L = 600 \Omega, C_L = 50 \text{pF}$	3.0 4.5 5.5	25 105 135	mV <sub>PP</sub>
		$R_L = 10k\Omega$ , $C_L = 10pF$	3.0 4.5 5.5	35 145 190	
_	Crosstalk Between Any Two Switches (Figure 12)	$f_{in}$ = Sine Wave; Adjust $f_{in}$ Voltage to Obtain 0dBm at $V_{IS}$ $f_{in}$ = 10kHz, $R_L$ = 600 $\Omega$ , $C_L$ = 50pF	3.0 4.5 5.5	-50 -50 -50	dB
		$f_{in} = 1.0MHz, R_L = 50\Omega, C_L = 10pF$	3.0 4.5 5.5	-60 -60 -60	
THD	Total Harmonic Distortion (Figure 14)	$\begin{split} f_{in} = 1 \text{kHz}, \ R_L = 10 \text{k}\Omega, \ C_L = 50 \text{pF} \\ \text{THD} = \text{THD}_{measured} - \text{THD}_{source} \\ V_{IS} = 2.0 \text{V}_{PP} \ \text{sine wave} \\ V_{IS} = 4.0 \text{V}_{PP} \ \text{sine wave} \\ V_{IS} = 5.0 \text{V}_{PP} \ \text{sine wave} \end{split}$	3.0 4.5 5.5	0.10 0.08 0.05	%

<sup>\*</sup>Limits not tested. Determined by design and verified by qualification.

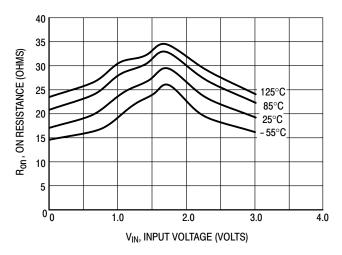


Figure 1a. Typical On Resistance,  $V_{CC} = 3.0 \text{ V}$ 

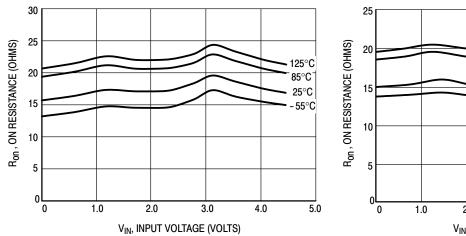


Figure 1b. Typical On Resistance,  $V_{CC} = 4.5 \text{ V}$ 

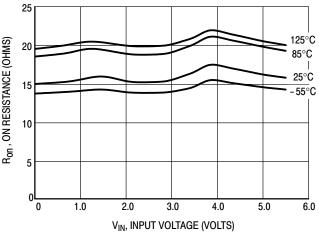


Figure 1c. Typical On Resistance,  $V_{CC} = 5.5 \text{ V}$ 

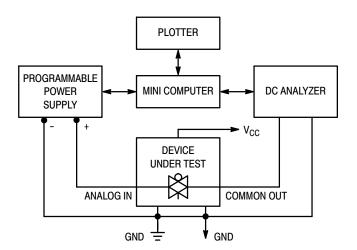


Figure 2. On Resistance Test Set-Up

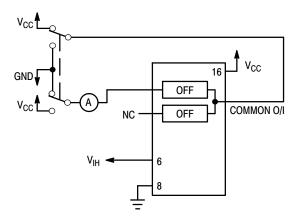


Figure 3. Maximum Off Channel Leakage Current, Any One Channel, Test Set-Up

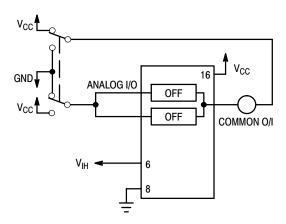


Figure 4. Maximum Off Channel Leakage Current, Common Channel, Test Set-Up

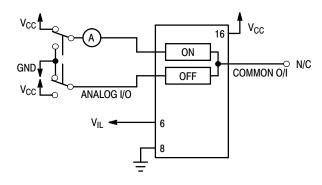


Figure 5. Maximum On Channel Leakage Current, Channel to Channel, Test Set-Up

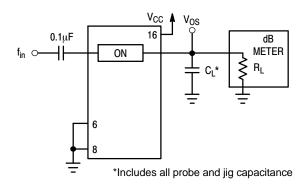


Figure 6. Maximum On Channel Bandwidth, Test Set-Up

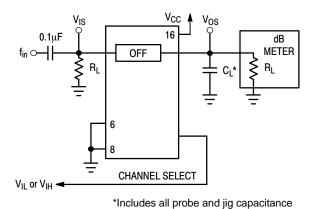
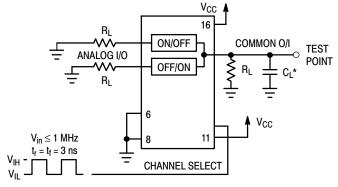


Figure 7. Off Channel Feedthrough Isolation, Test Set-Up



\*Includes all probe and jig capacitance

Figure 8. Feedthrough Noise, Channel Select to Common Out, Test Set-Up

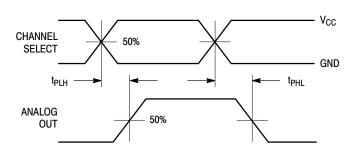
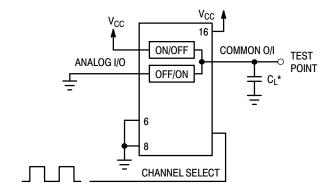


Figure 9a. Propagation Delays, Channel Select to Analog Out



\*Includes all probe and jig capacitance

Figure 9b. Propagation Delay, Test Set-Up Channel Select to Analog Out

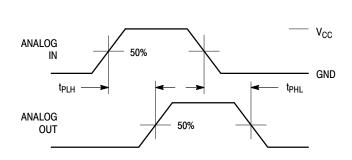
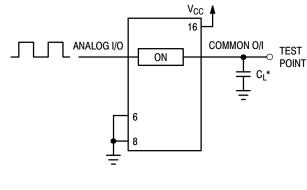


Figure 10a. Propagation Delays, Analog In to Analog Out



\*Includes all probe and jig capacitance

Figure 10b. Propagation Delay, Test Set-Up
Analog In to Analog Out

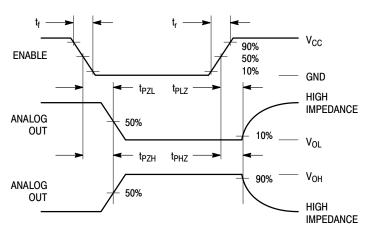


Figure 11a. Propagation Delays, Enable to Analog Out

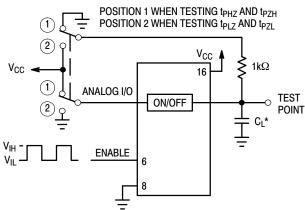
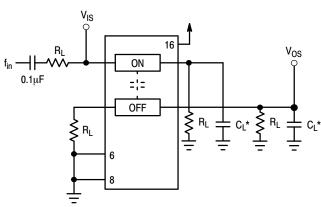


Figure 11b. Propagation Delay, Test Set-Up
Enable to Analog Out



\*Includes all probe and jig capacitance

Figure 12. Crosstalk Between Any Two Switches, Test Set-Up

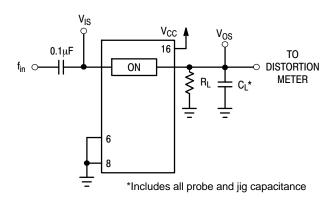


Figure 14a. Total Harmonic Distortion, Test Set-Up

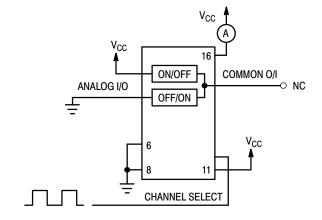


Figure 13. Power Dissipation Capacitance, Test Set-Up

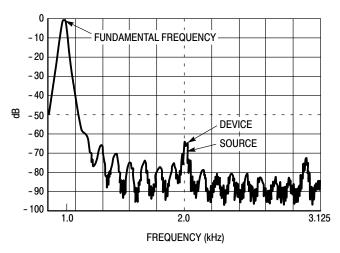


Figure 14b. Plot, Harmonic Distortion

# **APPLICATIONS INFORMATION**

The Channel Select and Enable control pins should be at  $V_{CC}$  or GND logic levels.  $V_{CC}$  being recognized as a logic high and GND being recognized as a logic low. In this example:

$$V_{CC} = +5V = logic \ high$$
  
 $GND = 0V = logic \ low$ 

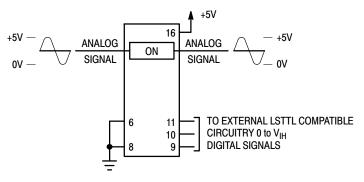
The maximum analog voltage swing is determined by the supply voltage  $V_{CC}$ . The positive peak analog voltage should not exceed  $V_{CC}$ . Similarly, the negative peak analog voltage should not go below GND. In this example, the difference between  $V_{CC}$  and GND is five volts. Therefore, using the configuration of Figure 15, a maximum analog signal of five volts peak—to—peak can be controlled. Unused analog inputs/outputs may be left floating (i.e., not

connected). However, tying unused analog inputs and outputs to  $V_{CC}$  or GND through a low value resistor helps minimize crosstalk and feedthrough noise that may be picked up by an unused switch.

Although used here, balanced supplies are not a requirement. The only constraints on the power supplies are that:

$$V_{CC} - GND = 2$$
 to 6 volts

When voltage transients above  $V_{CC}$  and/or below GND are anticipated on the analog channels, external Germanium or Schottky diodes  $(D_x)$  are recommended as shown in Figure 16. These diodes should be able to absorb the maximum anticipated current surges during clipping.



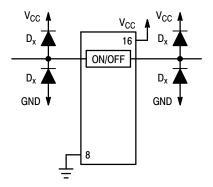
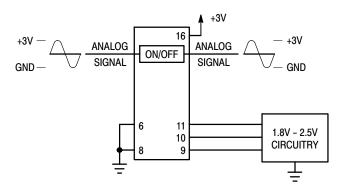
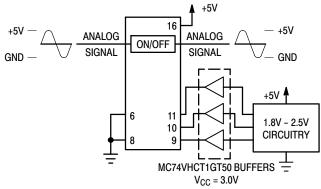


Figure 15. Application Example

Figure 16. External Germanium or Schottky Clipping Diodes

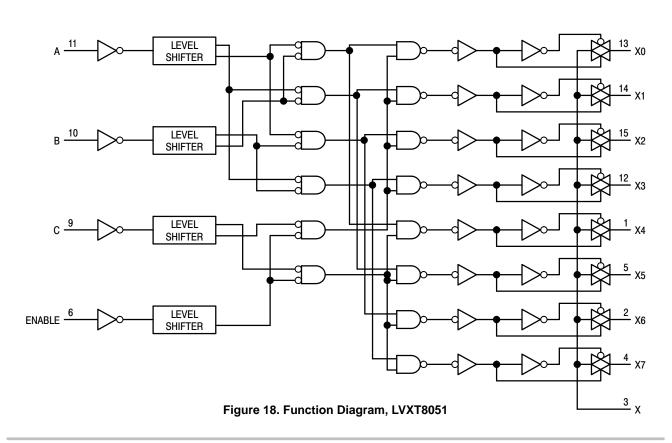




a. Low Voltage Logic Level Shifting Control

b. 2-Stage Logic Level Shifting Control

Figure 17. Interfacing to Low Voltage CMOS Outputs



# **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>	
MC74LVXT8051DG	SOIC-16 (Pb-Free)	48 Units / Rail	
MC74LVXT8051DR2G	SOIC-16 (Pb-Free)	2500 Tape & Reel	
MC74LVXT8051DTR2G	TSSOP-16 (Pb-Free)	2500 Tape & Reel	

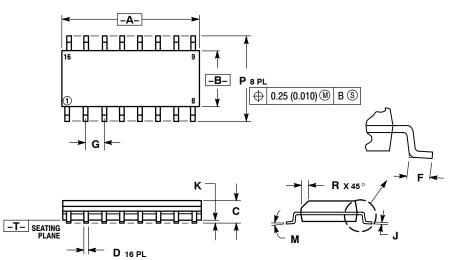
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.





# SOIC-16 CASE 751B-05 **ISSUE K**

**DATE 29 DEC 2006** 



⊕ 0.25 (0.010) M T B S A S

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETER.

  3. DIMENSIONS A AND B DO NOT INCLUDE MOLD ENGREPHING.
- PROTRUSION.

  MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- DIMENSION D DOES NOT INCLUDE DAMBAR
  PROTRUSION. ALLOWABLE DAMBAR PROTRUSION.
  SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D
  DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
U	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
7	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0°	7°	0°	7°	
P	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

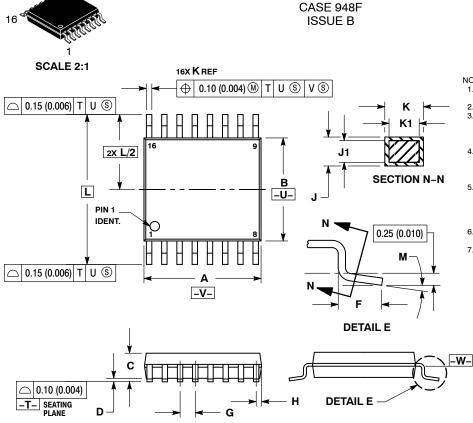
STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:		
	COLLECTOR	PIN 1.	CATHODE		COLLECTOR, DYE #1	PIN 1.	COLLECTOR, DYE #1	
2.	BASE	2.	ANODE	2.	BASE, #1	2.	COLLECTOR, #1	
3.	EMITTER	3.	NO CONNECTION	3.	EMITTER, #1	3.	COLLECTOR, #2	
4.	NO CONNECTION	4.	CATHODE	4.	COLLECTOR, #1	4.	COLLECTOR, #2	
5.	EMITTER	5.	CATHODE	5.	COLLECTOR, #2	5.	COLLECTOR, #3	
6.	BASE	6.	NO CONNECTION	6.	BASE, #2	6.	COLLECTOR, #3	
7.	COLLECTOR	7.	ANODE	7.	EMITTER, #2	7.	COLLECTOR, #4	
8.	COLLECTOR	8.	CATHODE	8.	COLLECTOR, #2	8.	COLLECTOR, #4	
9.	BASE	9.	CATHODE	9.	COLLECTOR, #3	9.	BASE, #4	
10.	EMITTER	10.	ANODE	10.	BASE, #3	10.	EMITTER, #4	
11.	NO CONNECTION	11.	NO CONNECTION	11.	EMITTER, #3	11.	BASE, #3	
12.	EMITTER	12.		12.	COLLECTOR, #3	12.	EMITTER, #3	
13.	BASE	13.	CATHODE	13.		13.	BASE, #2	RECOMMENDED
14.	COLLECTOR	14.	NO CONNECTION		BASE, #4	14.	EMITTER, #2	SOLDERING FOOTPRINT*
15.	EMITTER	15.	ANODE	15.	EMITTER, #4	15.	BASE, #1	
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1	8X
								<b>←</b> 6.40 <b>→</b>
STYLE 5:		STYLE 6:		STYLE 7:				
PIN 1.	DRAIN, DYE #1		CATHODE	PIN 1.	SOURCE N-CH			16X 1.12 < ➤
2.	DRAIN, #1	2.		2.	COMMON DRAIN (OUTPUT	Γ)		
3.	DRAIN, #2	3.	CATHODE	3.	COMMON DRAIN (OUTPU		1	1 16
4.	DRAIN, #2	4.	CATHODE	4.	GATE P-CH	- /	₩	
5.	DRAIN, #3	5.	CATHODE	5.	COMMON DRAIN (OUTPUT	Γ)		
6.	DRAIN, #3	6.	CATHODE	6.	COMMON DRAIN (OUTPU		16X 🛣	<b>—</b>
7.	DRAIN, #4	7.	CATHODE	7.			0.58	
8.	DRAIN, #4	8.	CATHODE	8.	SOURCE P-CH `	,	0.00	
9.	GATE, #4	9.	ANODE	9.	SOURCE P-CH			
10.	SOURCE, #4	10.	ANODE	10.	COMMON DRAIN (OUTPUT	Γ)	_	<u> </u>
11.	GATE, #3	11.	ANODE	11.	COMMON DRAIN (OUTPUT	Γ)		
12.	SOURCE, #3	12.	ANODE	12.	COMMON DRAIN (OUTPUT	Γ)		
13.	GATE, #2	13.	ANODE	13.	GATE N-CH			
14.	SOURCE, #2	14.	ANODE	14.	COMMON DRAIN (OUTPUT	Γ)		
15.	GATE, #1	15.	ANODE	15.	COMMON DRAIN (OUTPUT	Γ)		PITCH
16.	SOURCE, #1	16.	ANODE	16.	SOURCE N-CH			
								8
								Ţ
								DIMENSIONS: MILLIMETERS

\*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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TSSOP-16 WB

**DATE 19 OCT 2006** 

#### NOTES

- DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT
- EXCEED 0.15 (0.006) PER SIDE.
  DIMENSION B DOES NOT INCLUDE
  INTERLEAD FLASH OR PROTRUSION.
- INTERLEAD FLASH OR PROTRUSION.
  INTERLEAD FLASH OR PROTRUSION SHALL
  NOT EXCEED 0.25 (0.010) PER SIDE.
  DIMENSION K DOES NOT INCLUDE DAMBAR
  PROTRUSION. ALLOWABILE DAMBAR
  PROTRUSION SHALL BE 0.08 (0.003) TOTAL
  IN EXCESS OF THE K DIMENSION AT
  MAXIMUM MATERIAL CONDITION.
  TERMINIAL NILMBERS ADE SUCIUMI ECIP.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
М	0 °	8°	0°	8 °

# **RECOMMENDED** SOLDERING FOOTPRINT\*

# 7.06 ٦ 1 0.65 **PITCH** 16X 0.36 1.26 **DIMENSIONS: MILLIMETERS**

# **GENERIC** MARKING DIAGRAM\*



= Specific Device Code XXXX Α = Assembly Location

= Wafer Lot L = Year W = Work Week G or • = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present. Some products may not follow the Generic Marking.

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<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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